

**SPDT High Isolation Terminated Switch,
0.01 - 3.0 GHz**

**MASWSS0024
V6**

Features

- Positive Voltage Control: 0 / +5 V
- High Isolation: 55 dB typ. @ 0.9 GHz,
50 dB typ. @ 1.9 GHz
- 50-Ohm Internal Terminations
- Low Insertion Loss: 0.6 dB typ. @ 0.9 GHz,
0.7 dB typ. @ 1.9 GHz
- MSOP-8-EP Package

Description

The M/A-COM MASWSS0024 GaAs monolithic switch provides high isolation in a low-cost, plastic surface mount package. The MASWSS0024 is ideal for applications across a broad range of frequencies including synthesizer switching, transmit / receive switching, switch matrices and filter banks in systems such as radio and cellular equipment, PCS, GPS, and fiber optic modules.

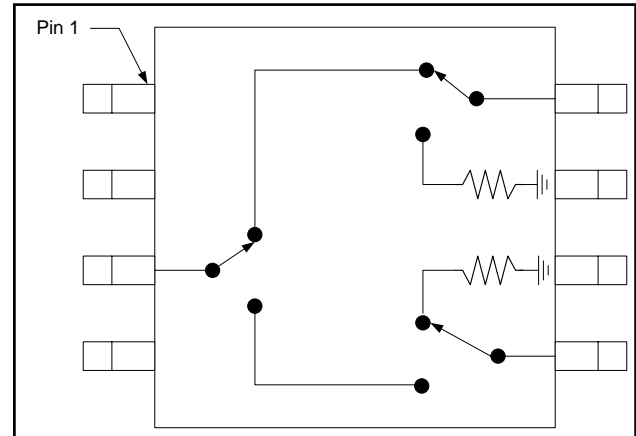
M/A-COM fabricates the MASWSS0024 using a 1.0-micron gate length MESFET process. The process features full chip passivation for performance and reliability.

Ordering Information¹

Part Number	Package
MASWSS0024	Bulk Packaging
MASWSS0024TR	1000 piece reel
MASWSS0024TR-3000	3000 piece reel
MASWSS0024SMB	Sample Board

1. Reference Application Note M513 for reel size information.

Functional Block Diagram



Pin Configuration²

Pin	Function	Pin	Function
1	V1	5	RF2
2	V2	6	Ground
3	RF Common	7	Ground
4	Ground	8	RF1

2. The exposed pad centered on the package bottom must be connected to RF and DC ground.

Absolute Maximum Ratings^{3,4}

Parameter	Absolute Maximum
Input Power (0.5 - 3.0 GHz) 3V Control 5V Control	+30 dBm +33 dBm
Operating Voltage	+8.5 Volts
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

3. Exceeding any one or combination of these limits may cause permanent damage to this device.

4. M/A-COM does not recommend sustained operation near these survivability limits.

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Electrical Specifications ⁵: T_A = 25°C, V_{CTL} = 0, 5.0V (unless otherwise specified)

Parameter	Test Conditions	Units	Min	Typ	Max
Insertion Loss	0.01 - 0.5 GHz	dB	—	0.5	—
	0.5 - 1.0 GHz	dB	—	0.6	0.7
	1.0 - 2.0 GHz	dB	—	0.7	0.8
	2.0 - 3.0 GHz	dB	—	0.75	0.9
Isolation	0.01 - 0.5 GHz	dB	—	59	—
	0.5 - 1.0 GHz	dB	51	54	—
	1.0 - 2.0 GHz	dB	48	52	—
	2.0 - 3.0 GHz	dB	43	48	—
Return Loss	0.01 - 0.5 GHz ⁶	dB	—	20	—
	0.5 - 1.0 GHz	dB	—	20	—
	1.0 - 2.0 GHz	dB	—	20	—
	2.0 - 3.0 GHz	dB	—	20	—
Input IP ₂	2-Tone 900 MHz, 5 MHz spacing (V _C = 5.0V)	dBm	—	83	—
Input IP ₃	2-Tone 900 MHz, 5 MHz spacing (V _C = 5.0V)	dBm	—	43	—
Trise, Tfall	10% to 90% RF & 90% to 10% RF	nS	—	24	—
Ton, Toff	50% of V _C to 10% / 90% RF	nS	—	15	—
Transients	V _C = 5.0V square wave, in-band	mV	—	12	—

5. External DC blocking capacitors are required on all RF ports (47 pF capacitors are recommended). Use larger value capacitors for lower frequency operation (e.g. use 10,000 pF capacitors to optimize insertion and return loss at frequencies below 50 MHz).

6. Terminated return loss is governed by blocking capacitors internal to the device; see applications plot.

Truth Table

V1	V2	RFC-RF1	RFC-RF2
0	1	Off	On
1	0	On	Off

Logic Level	Voltage Level ⁷
V _{LO} "0"	0 ± 0.2V
V _{HIGH} "1"	V _C ± 0.2V

7. 3.0V ≤ V_C ≤ 8.0V

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

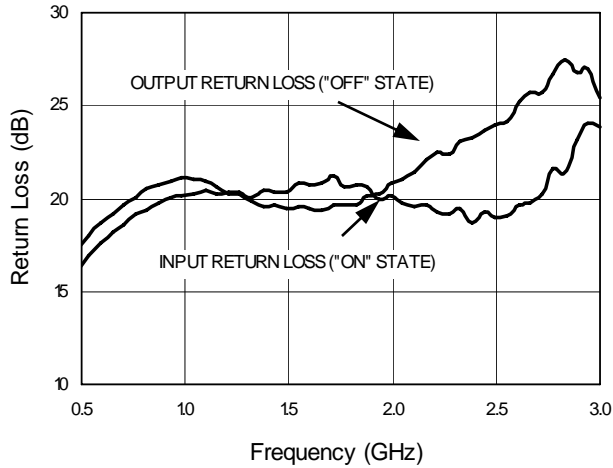
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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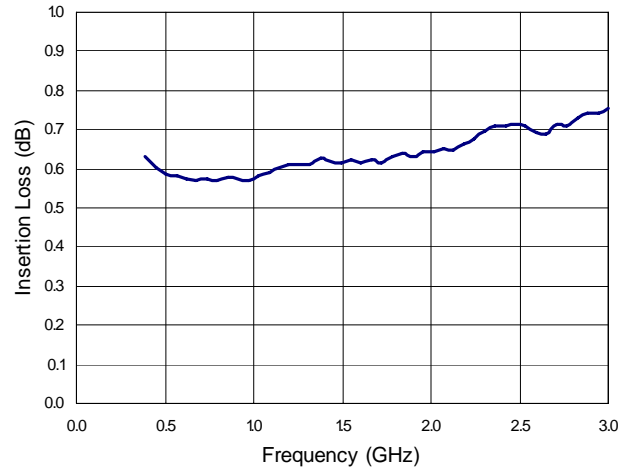
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Typical Performance Curves

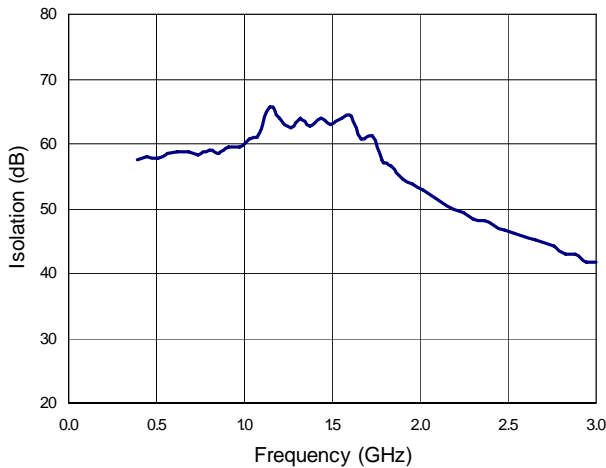
Return Loss vs. Frequency



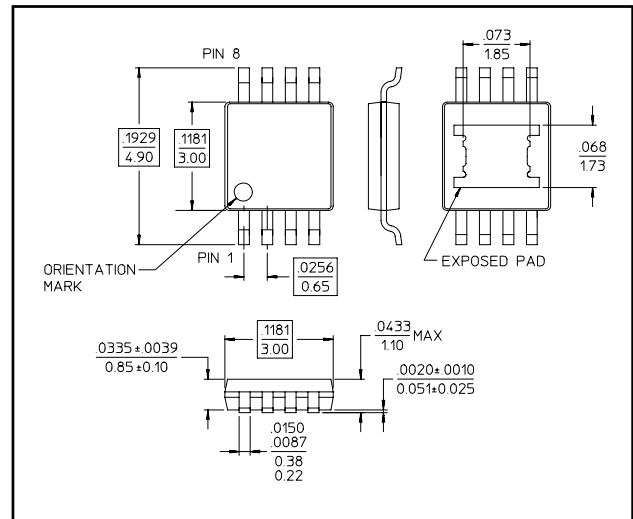
Insertion Loss vs. Frequency



Isolation vs. Frequency



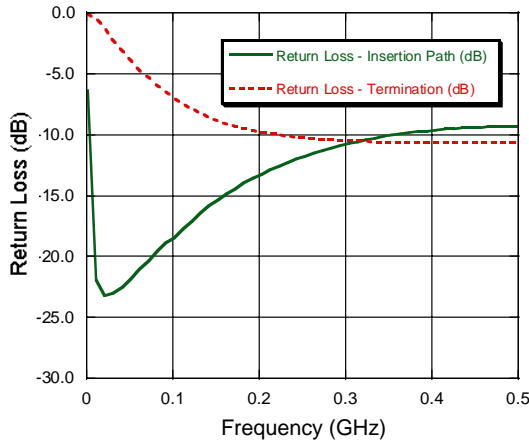
MSOP-8-EP



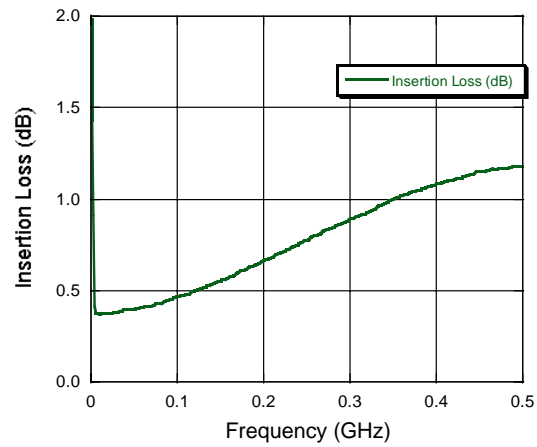
Applications Section

Typical Performance Curves, Very Low Frequency, 10000 pF Blocking Capacitors

Return Loss vs. Frequency



Insertion Loss vs. Frequency



Isolation vs. Frequency

